

Title (en)

METHOD FOR GROWING THIN SEMICONDUCTOR RIBBONS

Title (de)

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Title (fr)

PROCEDE DE TIRAGE DE RUBANS DE SEMI-CONDUCTEUR DE FAIBLE EPAISSEUR

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Application

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Abstract (en)

[origin: WO2006111668A1] The invention relates to a method for growing at least one ribbon made of a semiconductor material (40-42) according to which two parallel and interspaced filaments (24-26) vertically pass through, upward and at a continuous speed, the surface of a bath of this molten semiconductor material, the ribbon (40-42) being formed from a meniscus located between the filaments and essentially at the level of said surface. According to the invention, a supporting strip (22) is placed between the filaments (24-26), the supporting strip (22) vertically passing through, upward and at a continuous speed, the surface of the molten semiconductor material at the same speed as the filaments, the semiconductor ribbon (40-42) thus being formed on one of the two sides of the supporting strip and being supported by this side. The invention serves to produce polycrystalline silicon ribbons for manufacturing photovoltaic cells.

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